

Sheet <u>1</u> of <u>1</u>

Form PTO-1449 U.S. Department of Commerce (Rev. 8-83) Patent and Trademark Office							Atty. Docket No.: 0756-945 Serial No.: 08/169				9,127			
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Sheet 1 of 1 Serial No. 08/169,127 Atty.Docket No. 0756-945 U.S. Department of Commerce Form PTO-1449 Patent and Trademark Office (Rev. 8-83) T Applicant Hisato SHINOHARA et al. INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary) Group Filing Date December 20, 1993 1112 U.S. PATENT DOCUMENTS Class Subclass-Filing Date Date Name Document Number Examiner (if Initial appropriate) 1980 JUM Miyaka et al. 427 53.1 3 1981 Sept 427 53.1 9 2 Hanak 2 ... :NJ 1983 NOV 427 53.1′ " 3 2 0 McKee et al. 4 4 1 0 1987 July 5 Yamazaki et al. 156 1643 9 Q 8 0 8 6 1987 Jue 5 8 Yamazaki et al. 427 53.1 1988 Jul 12/4/86 4 7 5 3 8 5 5 Haluska et al. 427 58 1988 JUNE 1/2/87 5 3 8 5 6 Haluska et al. 427 53.1 1988 1100. 156 643 8/7/87 8 5 8 Yamazaki et al. 7 6 3 FOREIGN PATENT DOCUMENTS Class Subclass Translation Country Date Document Number Yes No no such number in previono clae 1982 Japan 3 1982 8 2 Japan 9 5 1988 1 8 Japan OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Date Considered Examiner. *EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

U.S.Department of Commerce Form PTO-1449 Atty Docket 0756-0945 Serial No. 08/169,127 Patent and Trademark Office (Rev. 8-83) Applicants: Hisato SHINOHARA et al. INFORMATION DISCLOSURE STATEMENT Filing Date: December 20, 1993 Gr up Art Unit: 1762 SEP 0 9 2002 **U.S. PATENT DOCUMENTS** RADEMAR Scument Number Filing Date Name Class Subclass Date Examiner (if appropriate) Initial 11/12/1974 Locke 3,848,104 04/15/1975 Glenn, Jr. 3,877,777 05/15/1979 Connolly, Jr. et al. 4,154,530 07/27/1982 Yaron et al. 4,341,569 11/09/1982 Spohnheimer 4,358,659 RECEIVED 01/25/1983 Levatter 4,370,175 Neiheisel 08/28/1984 4,468,551 ISEP 1 | 1 2002 Takeuchi 09/24/1985 4,543,464 10/17/1989 Yamazaki et al. 4,874,920 06/26/1990 Yamazaki 4,937,129 11/13/1990 Yamazaki et al. 4,970,368 Yamazaki et al. 4,970,369 11/13/1990 04/26/1994 Masumo et al. 5,306,651 Zhang et al. 06/14/1994 5,320,984 07/11/1995 Hong 5,432,112 09/26/1995 Yamazaki 5,453,858 04/27/1999 Yamazaki et al. 5,897,799 Yamazaki et al. 12/14/1999 6,002,101 11/21/2000 Shinohara et al. 6,149,988 **FOREIGN PATENT DOCUMENTS** Subclass Translation Class Document Number Date Country Examiner Yes Initial Full Eng 06/28/1989 EP 0 322 258 Full Eng 09/26/1989 JP 01-241862 Full Eng 11/25/1992 JP 04-338631 Full Eng 01/29/1993 JP 05-021339 Full Eng 03/06/1980 JP 55-032026 Eng Abst 05/19/1982 JP 57-079914 Full Eng 12/04/1985 JP 60-245124 Full Eng 12/19/1985 JP 60-257511 Full Eng 04/24/1986 JP 61-080815 Date Considered Examiner *EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this formwith next communication to applicant.

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